SKKT 330, SKKH 330

SEMIPACK® 3 [1)]

Thyristor / Diode Modules

SKKH 330

SKKT 330

Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

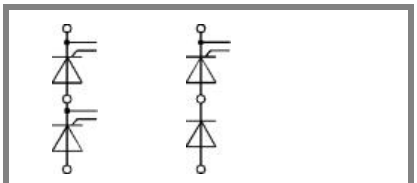
1) Discontinued version, redesigned version already available

2) See the assembly instruction

3) The screws must be lubricated

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 510 A (maximum value for continuous operation) I_{TAV} = 330 A (sin. 180; T_c = 80 °C)	
900	800	SKKT 330/08E	SKKH 330/08E
1300	1200	SKKT 330/12E	SKKH 330/12E
1500	1400	SKKT 330/14E	SKKH 330/14E
1700	1600	SKKT 330/16E	SKKH 330/16E
1900	1800	SKKT 330/18E	SKKH 330/18E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 85 (100) °C	305 (225)	A
I_D	P16/200F; T_a = 35 °C; B2 / B6	520 / 650	A
I_{RMS}	P16/200F; T_a = 35 °C; W1 / W3	585 / 3 * 485	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	9500	A
	T_{vj} = 130 °C; 10 ms	8000	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	451000	A²s
	T_{vj} = 130 °C; 8,3 ... 10 ms	320000	A²s
V_T	T_{vj} = 25 °C; I_T = 750 A	max. 1,4	V
$V_{T(TO)}$	T_{vj} = 130 °C	max. 0,8	V
r_T	T_{vj} = 130 °C	max. 0,6	mΩ
I_{DD}; I_{RD}	T_{vj} = 130 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 50	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 130 °C	max. 250	A/µs
$(dv/dt)_{cr}$	T_{vj} = 130 °C	max. 1000	V/µs
t_q	T_{vj} = 130 °C	50 ... 150	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 500	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ. / max.	300 / 2000	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 3	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 200	mA
V_{GD}	T_{vj} = 130 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 130 °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,11 / 0,055	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,116 / 0,058	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,13 / 0,065	K/W
$R_{th(c-s)}$	per thyristor / per module	0,04 / 0,02	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 40 ... + 130	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 %[2)]	Nm
M_t	to terminals	9 ± 15 %[3)]	Nm
a		5 * 9,81	m/s²
m	approx.	750	g
Case	SKKT	A 73a	
	SKKH	A 76a	



SKKT SKKH

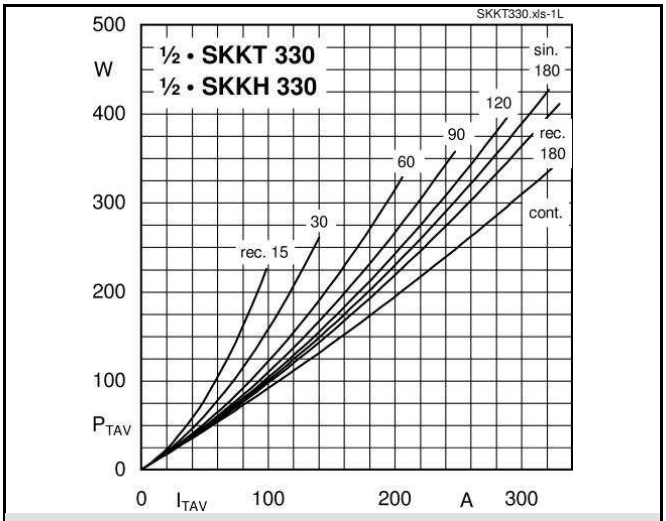


Fig. 1L Power dissipation per thyristor vs. on-state current

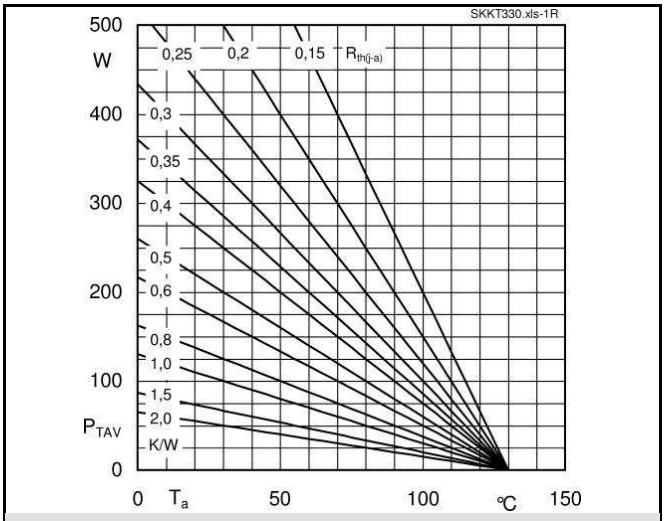


Fig. 1R Power dissipation per thyristor vs. ambient temp.

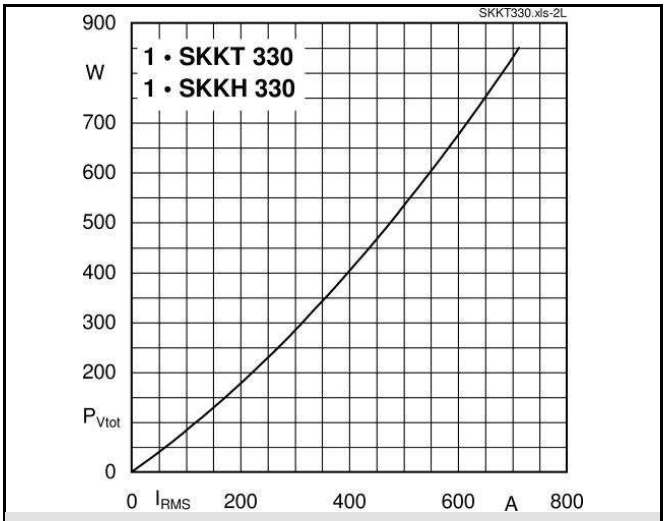


Fig. 2L Power dissipation per module vs. rms current

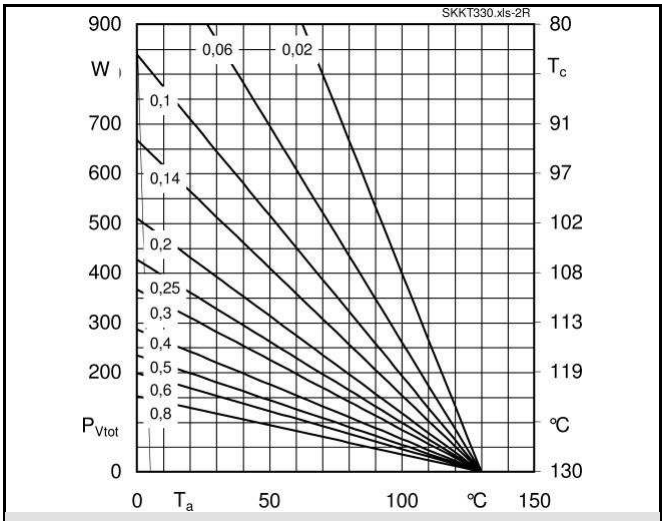


Fig. 2R Power dissipation per module vs. case temp.

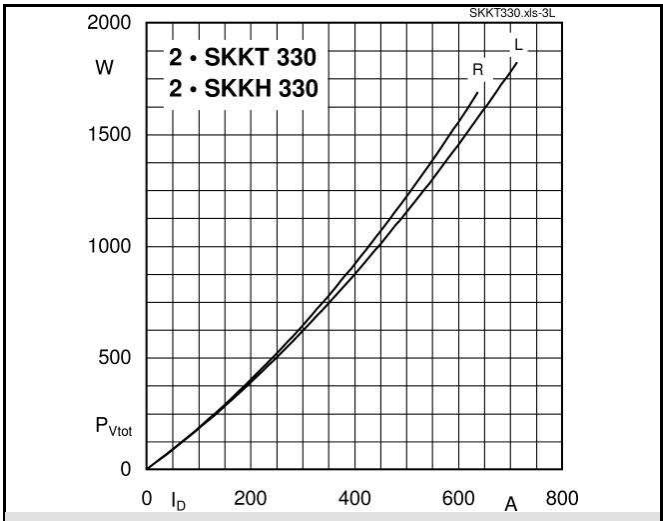


Fig. 3L Power dissipation of two modules vs. direct current

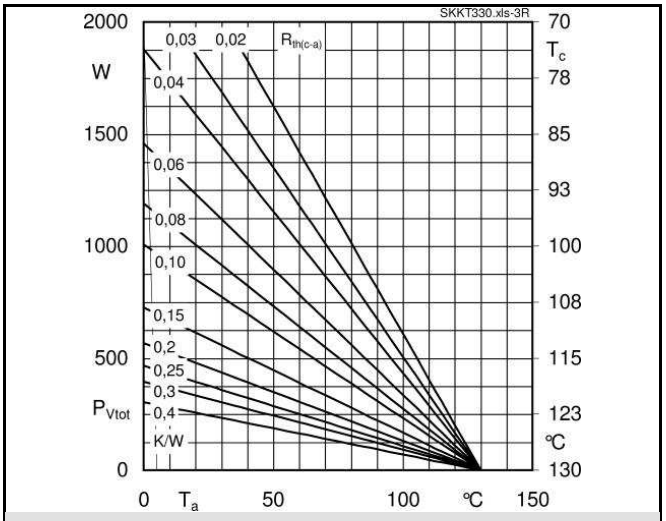


Fig. 3R Power dissipation of two modules vs. case temp.

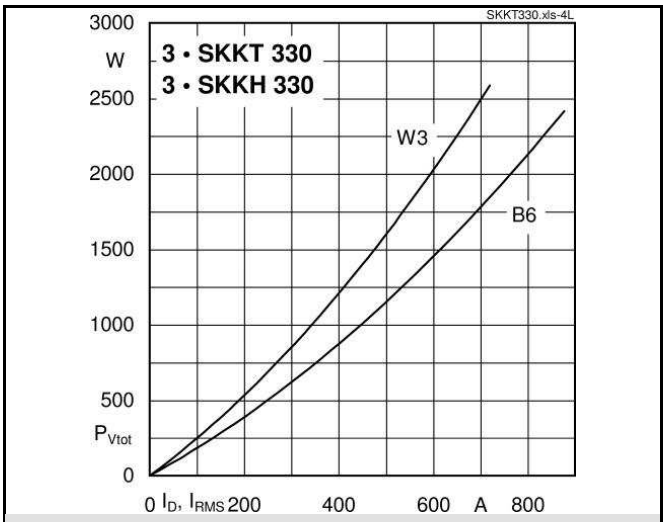


Fig. 4L Power dissipation of three modules vs. direct and rms current

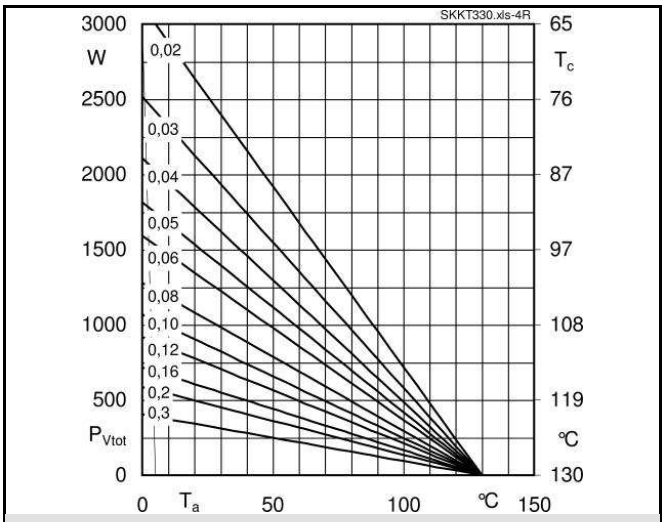


Fig. 4R Power dissipation of three modules vs. case temp.

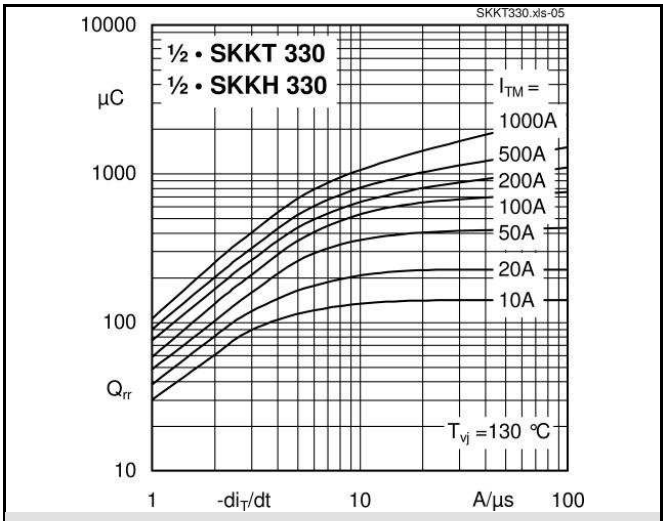


Fig. 5 Recovered charge vs. current decrease

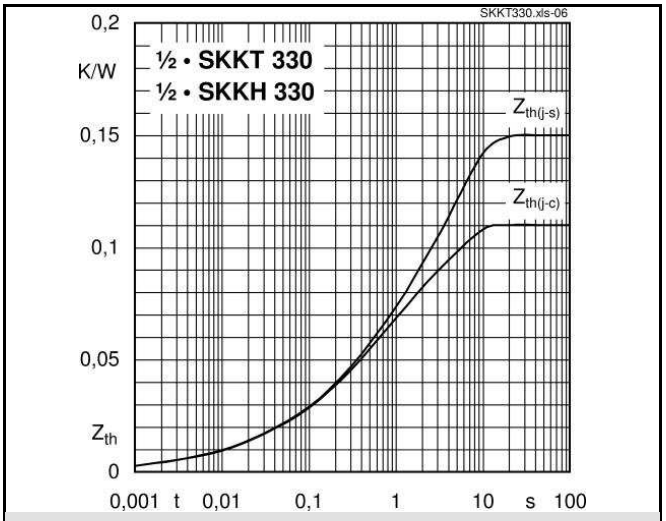


Fig. 6 Transient thermal impedance vs. time

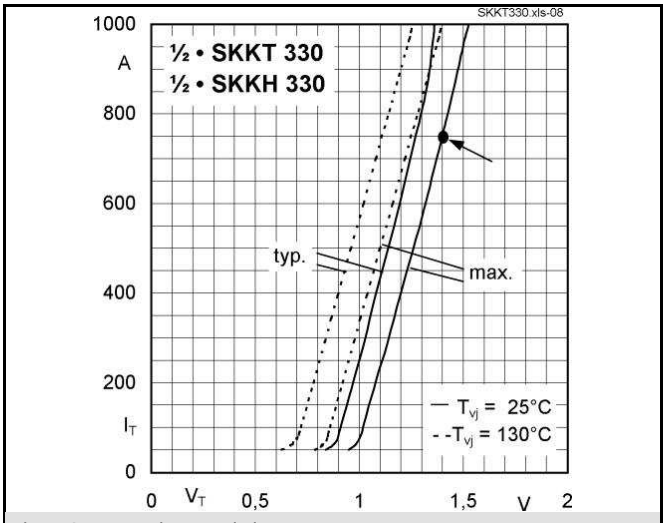


Fig. 7 On-state characteristics

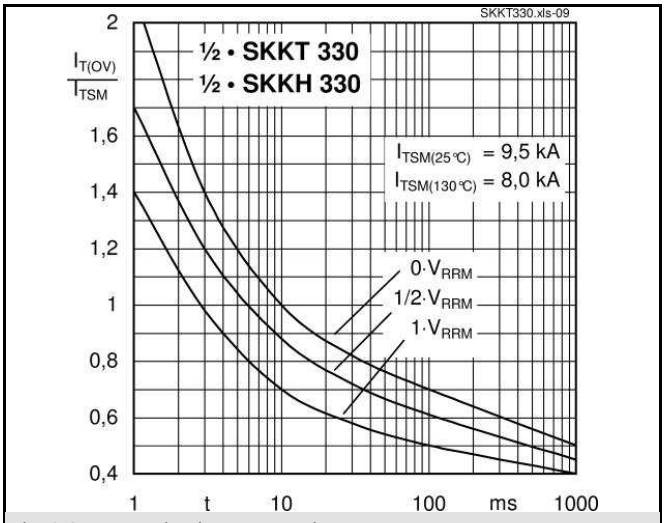


Fig. 8 Surge overload current vs. time

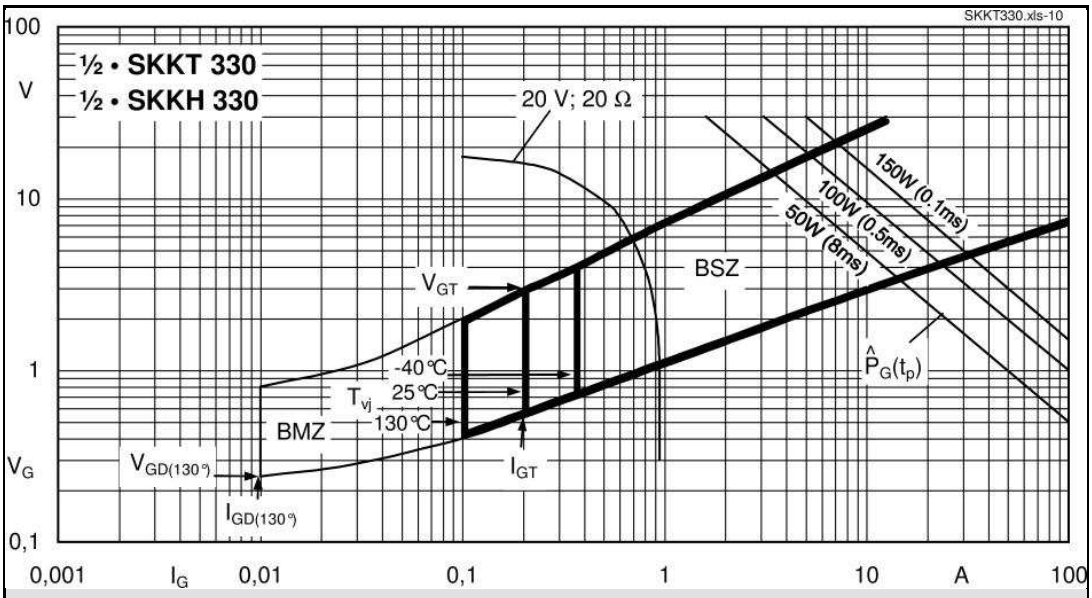
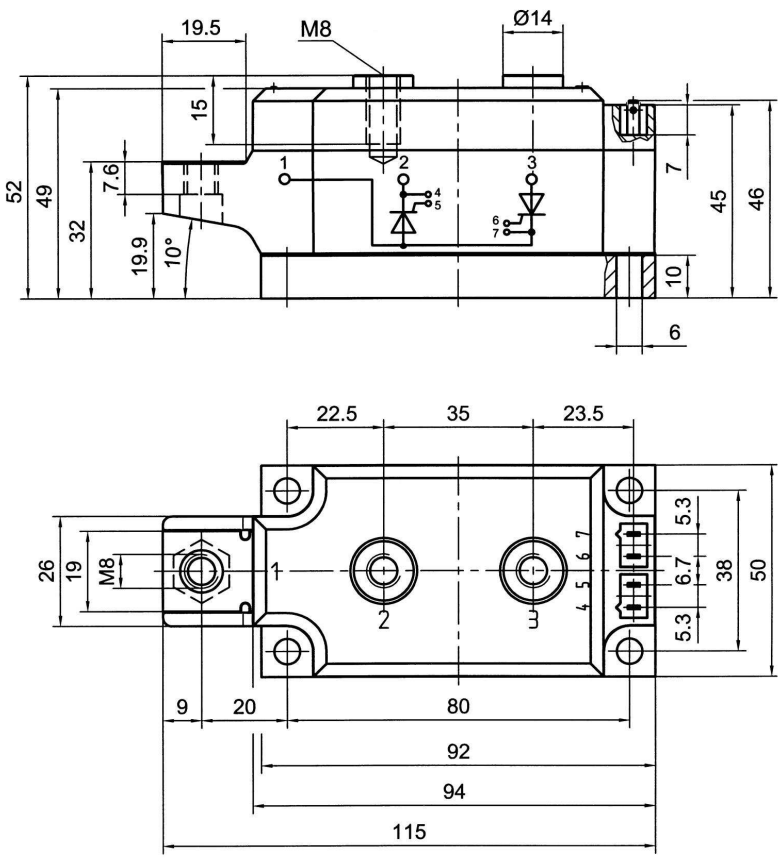
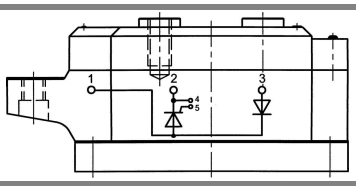


Fig. 9 Gate trigger characteristics

Dimensions in mm



Case A 73a (SKKT)



Case A 76a SKKH

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